

#### **Thermal Performance**

Parameter			Symbol	Limit			Unit
Thermal Resistance - Junction to Case		TO-220	RƏ <sub>JC</sub>		1.0		°C 44/
		ITO-220			4.2		°C/W
Thermal Resistance - Junction to Ambient			RƏ <sub>JA</sub>		62.5		°C/W
Note: Surface mounted on FR4 board	t ≤ 10sec						
Electrical Specifications (Ta = 2	25°C unless o	otherwise note	d)				
Parameter	Con	ditions	Symbol	Min	Тур	Max	Unit
Static	1						
Drain-Source Breakdown Voltage	$V_{GS} = 0V,$	I <sub>D</sub> = 250uA	BV <sub>DSS</sub>	650			V
Drain-Source On-State Resistance	$V_{GS} = 10V$	, I <sub>D</sub> = 3Α	R <sub>DS(ON)</sub>		1.0	1.2	Ω
Gate Threshold Voltage	$V_{DS} = V_{GS}$	, I <sub>D</sub> = 250uA	V <sub>GS(TH)</sub>	2.0		4.0	V
Zero Gate Voltage Drain Current	$V_{DS} = 650^{\circ}$	V, $V_{GS} = 0V$				1	
	$V_{DS} = 650V, V_{GS} = 0V,$ $T_{C}=125^{\circ}C$		I <sub>DSS</sub>			50	uA
Forward Transfer Conductance	$V_{DS} = 8V,$	I <sub>D</sub> = 1A	<b>g</b> <sub>fs</sub>		3.7		S
Diode Forward Voltage	$I_{\rm S}$ = 6A, $V_{\rm C}$	<sub>3S</sub> ≠ 0V	$V_{SD}$			1.6	V
Dynamic		•					
Total Gate Charge	200		Qg		32	46	
Gate-Source Charge	$V_{DS} = 300V, I_D = 6A,$ $V_{GS} = 10V$		Q <sub>gs</sub>		6		nC
Gate-Drain Charge			$Q_gd$		11		
Input Capacitance	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1.0MHz		C <sub>iss</sub>		905		pF
Output Capacitance			C <sub>oss</sub>		115		
Reverse Transfer Capacitance			C <sub>rss</sub>		25		
Switching							
Turn-On Delay Time			t <sub>d(on)</sub>		14		
Turn-On Rise Time	$V_{GS} = 10V, I_D = 6A,$ $V_{DD} = 300V, R_G = 25\Omega$		t <sub>r</sub>		14		nS
Turn-Off Delay Time			t <sub>d(off)</sub>		47		
Turn-Off Fall Time			t <sub>f</sub>		19		
Reverse Recovery Time	$V_{GS} = 0V,$	I <sub>S</sub> = 6A,	t <sub>fr</sub>		638		nS
Reverse Recovery Charge	$dI_F/dt = 10$	00A/us	Q <sub>fr</sub>		4.8		uC

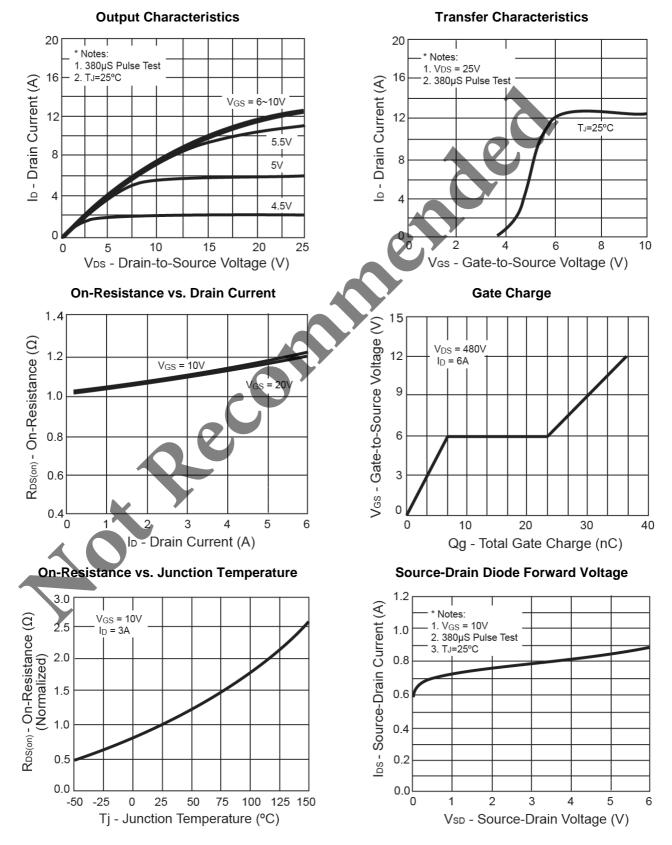
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2.  $V_{DD} = 50V$ ,  $I_{AS}=3.6A$ , L=30mH,  $V_{DS}=500V$ 3. Pulse test: pulse width ≤300uS, duty cycle ≤2%

4. Essentially Independent of Operating Temperature

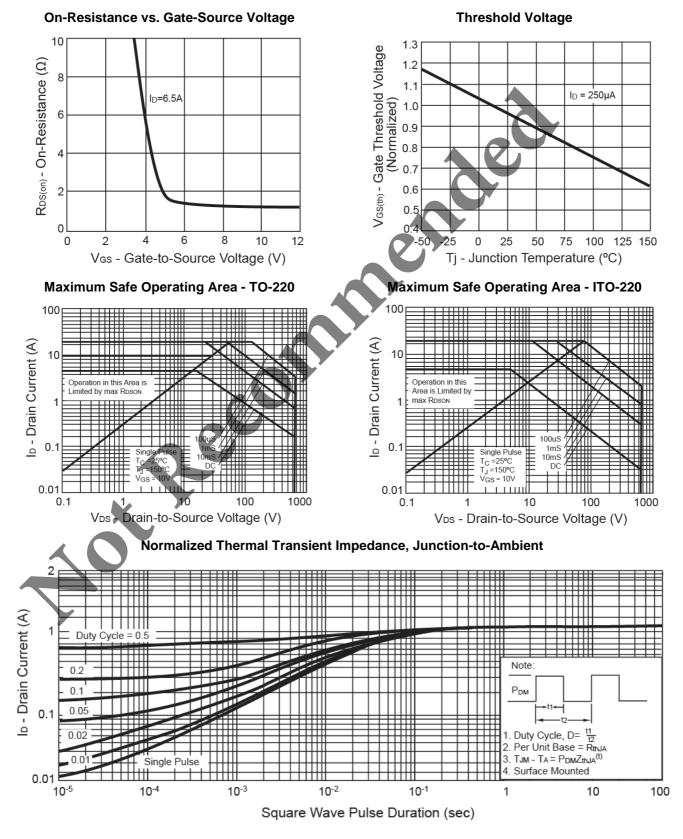


#### Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)



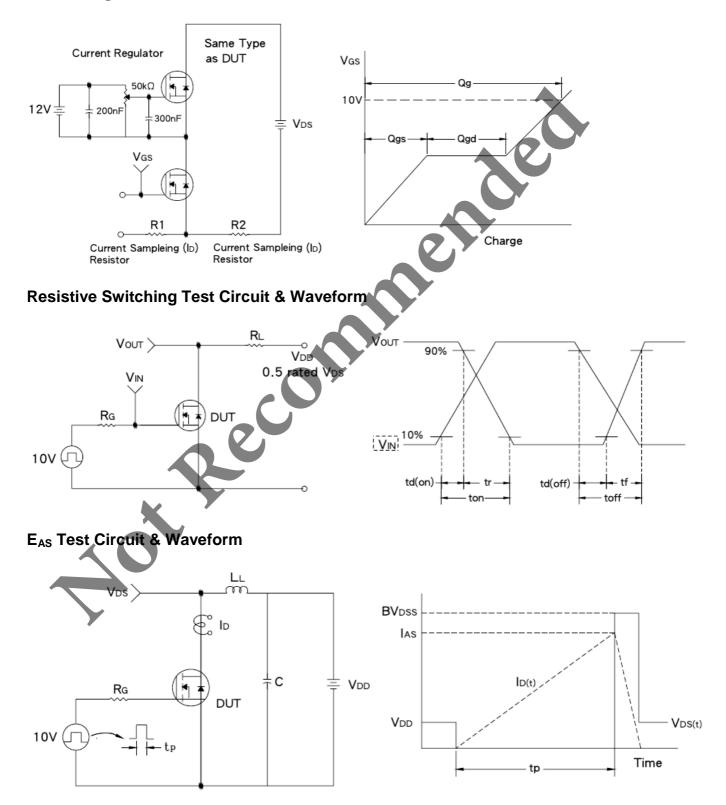


#### Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)



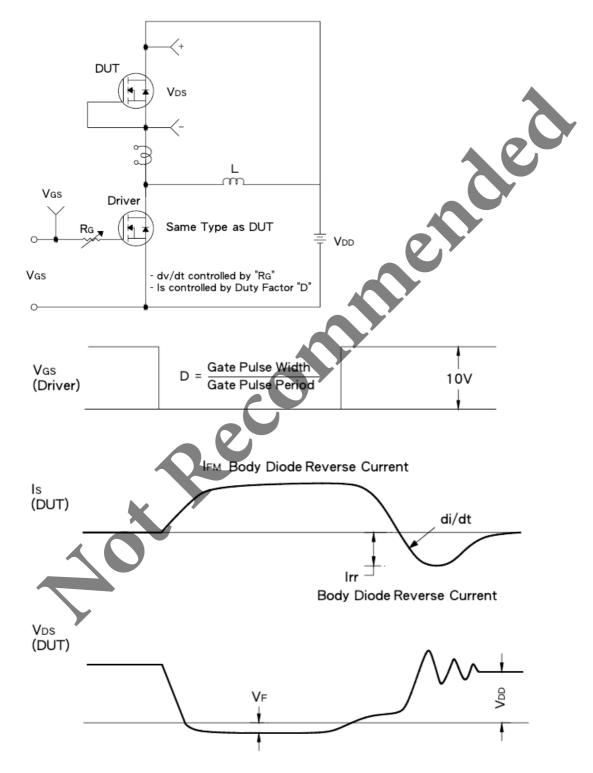


### Gate Charge Test Circuit & Waveform



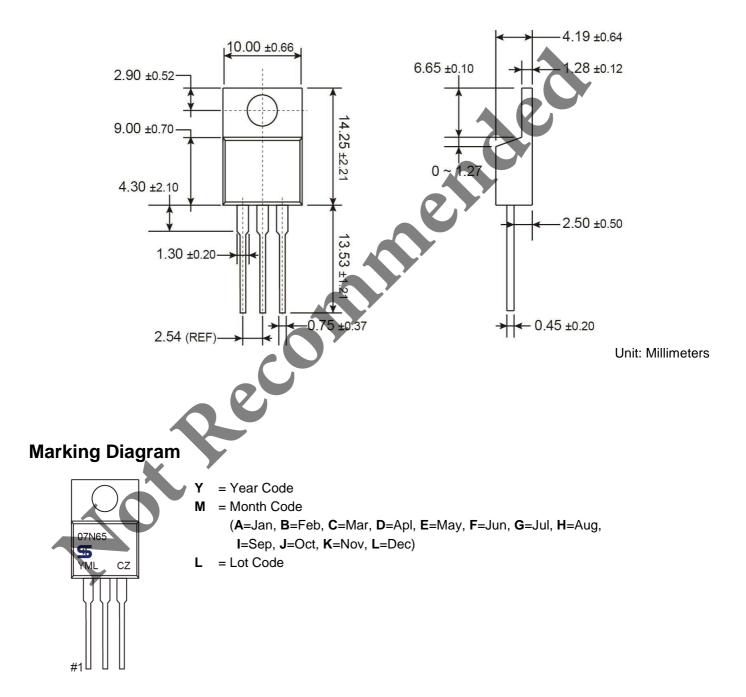


### Diode Reverse Recovery Time Test Circuit & Waveform



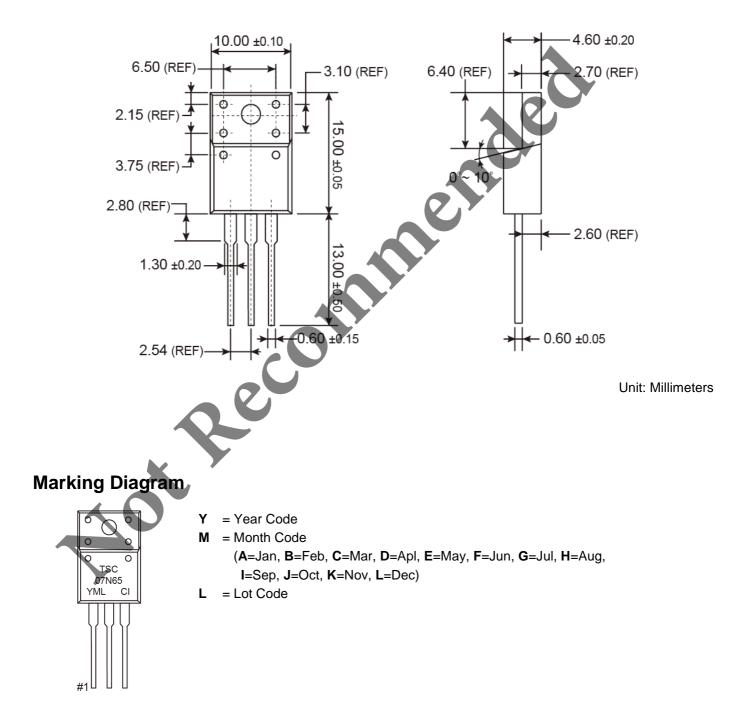


## **TO-220 Mechanical Drawing**





## **ITO-220 Mechanical Drawing**







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